

Title (en)
FORMATION AND TREATMENT OF A SIGE STRUCTURE

Title (de)
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Title (fr)
FORMATION ET TRAITEMENT D'UNE STRUCTURE EN SIGE

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Abstract (en)
[origin: WO2006077216A2] The invention relates to a method for forming a structure (30) provide with a layer (2) removed from a donor plate (10) comprising, prior to removal, a first Si_{1-x}Ge_x layer (1) and a second layer (2) placed on the first Si_{1-y}Ge_y layer (1) (x and y ranges, respectively, from 0 to 1, and x differs from y). The inventive method consists: a) in implanting atomic species in such a way that an embrittlement area (4) under the second (2), b) in gluing the donor plate (10) to a receiving plate (20), c) in heating for detaching the removed layers (1', 2) from the donor plate (10) in the embrittlement area (4), d) in carrying out a rapid thermal annealing (also called RAT) at a temperature equal to or greater than about 1000 °C for a time equal to or less than 5 minutes and e) in selectively etching the remaining part of the first layer (1') in front of the second layer (2).

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JP 2003168789 A 20030613 - SHINETSU HANDOTAI KK

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